

# A Time-over-Threshold asynchronous front-end in 28 nm CMOS for the readout of pixel detectors in extreme radiation environments

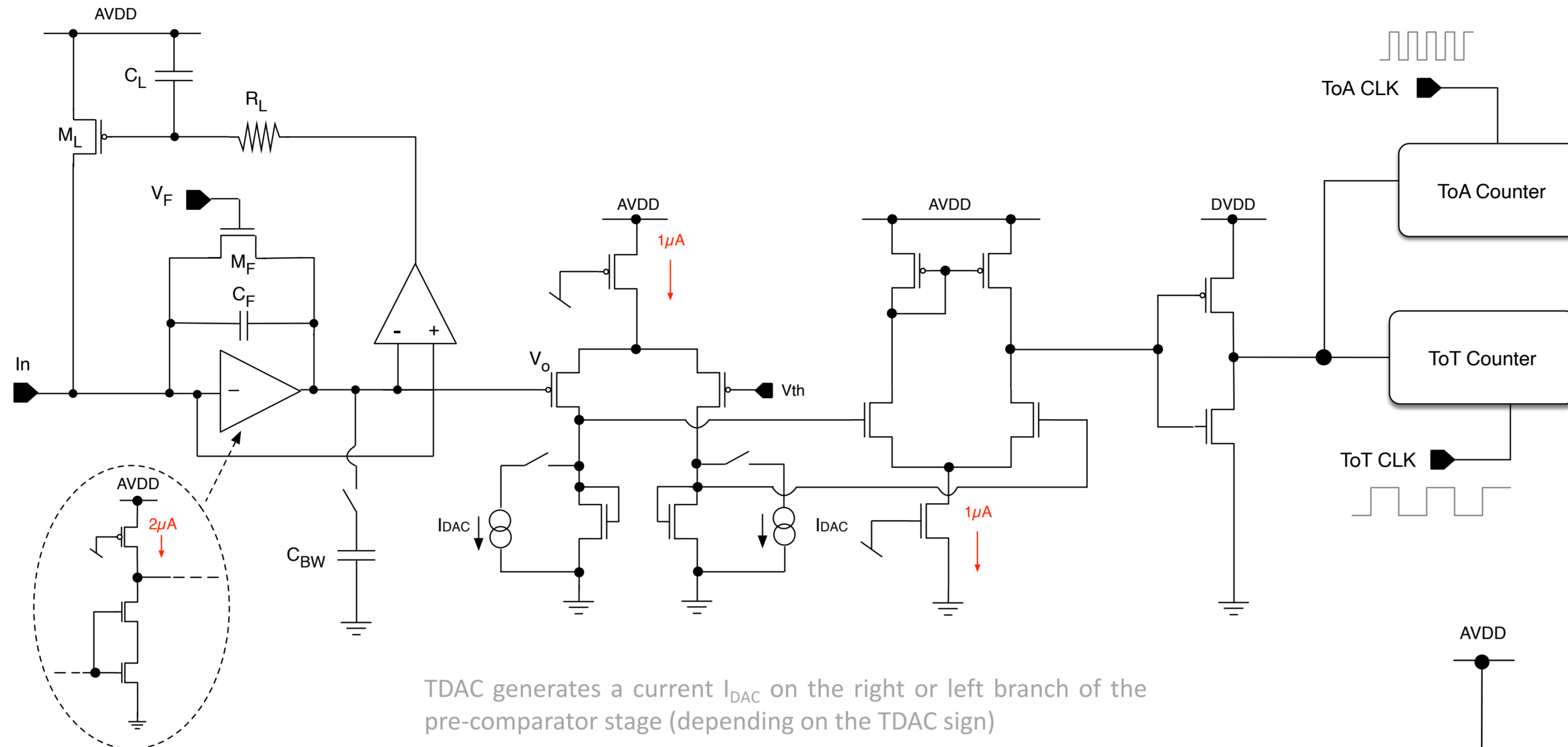
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## Introduction

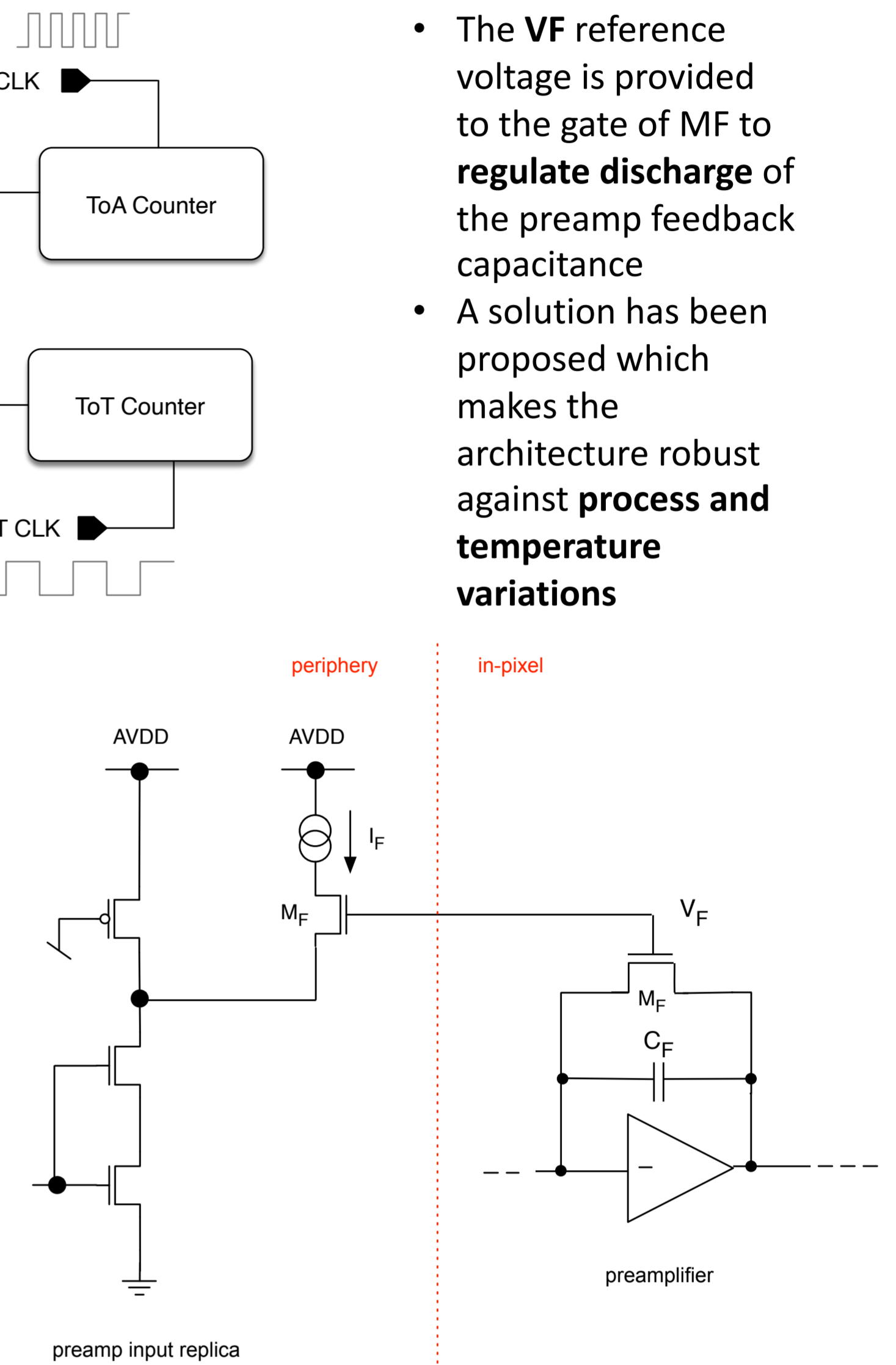
Advanced pixel readout chips have been developed by the CERN RD53 collaboration with a 65 nm CMOS technology. These chips have successfully met the stringent performance requirements of the ATLAS and CMS pixel detectors at the High-Luminosity Large Hadron Collider (HL-LHC). Looking towards future developments, the high-energy physics (HEP) microelectronics community is now focusing on the 28 nm CMOS technology. The work presented here addresses the design of analog front-end detectors based on the 28 nm process. Specifically, this research is part of the PRIN PiHEX project (funded by the Italian Ministry of University and Research), which represents a natural continuation of the INFN Falaphel project. Building upon the progress achieved in the latter, in particular in the field of radiation-hard electronics, PiHEX aims to further advance the state-of-the-art in pixel readout chip technology for high-luminosity colliders and next-generation X-ray imagers.

## The analog front-end



TDAC generates a current  $I_{DAC}$  on the right or left branch of the pre-comparator stage (depending on the TDAC sign)

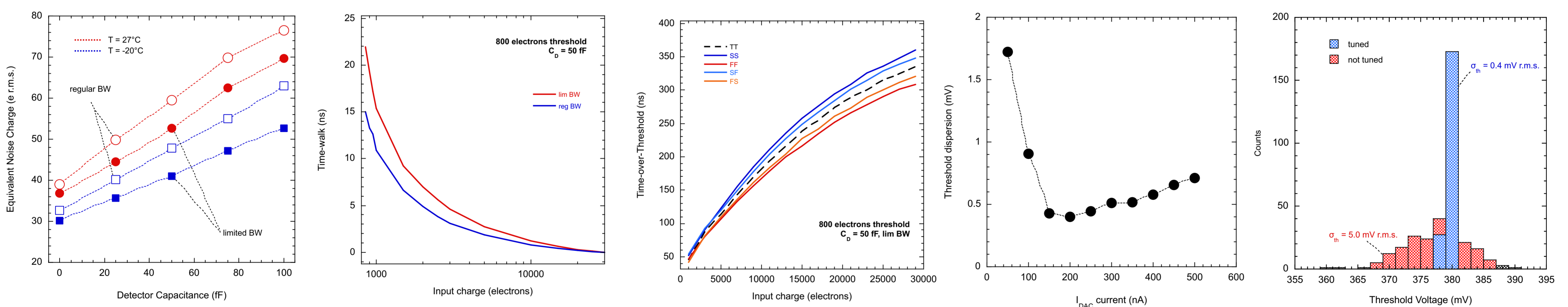
- preamplifier with detector leakage compensation circuit
- preamp bandwidth can be limited by loading its output with a 20 fF MoM capacitor ( $C_{BW}$ )
- 5-bit (+ 1 bit sign) threshold tuning DAC (TDAC)
- differential input pair loaded with diode connected transistors → single-ended to differential signal conversion (to improve the immunity to interferences)
- standard differential pair with active load + output inverter
- Time-over-Threshold counter for A/D conversion of the signal
- Time-of-Arrival counter for time-walk measurements



- The VF reference voltage is provided to the gate of MF to regulate discharge of the preamp feedback capacitance
- A solution has been proposed which makes the architecture robust against process and temperature variations

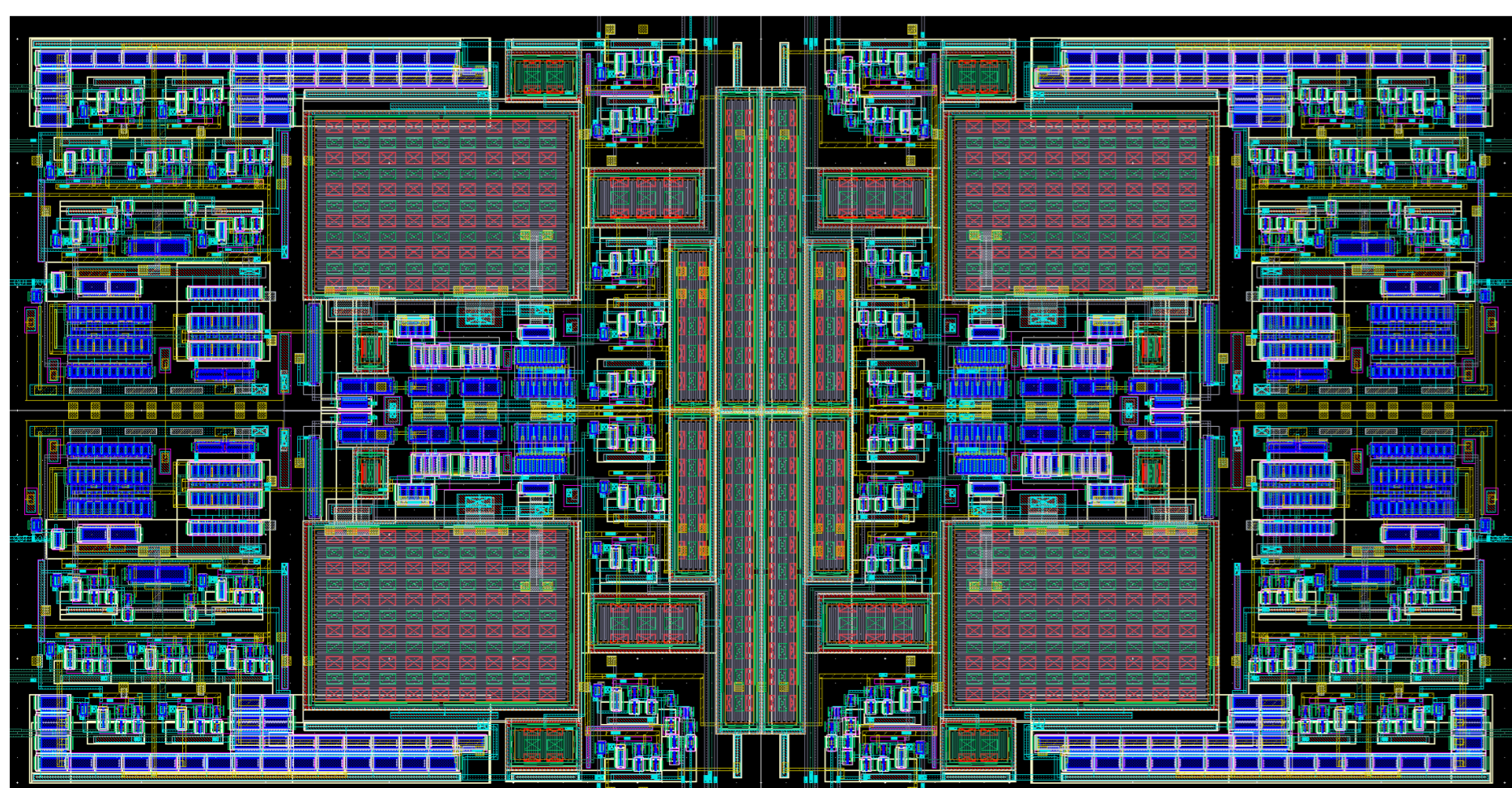
can possibly be distributed along matrix columns (1 every  $n$  pixels) to compensate for IR drops

## Main simulation results



- ENC as a function of detector cap for regular and limited preamp BW (room T and  $-20^\circ\text{C}$ )
- Time walk < 15 ns for the regular BW version
- ToT as a function of the input charge ( $\sim$ linear up to 12 ke<sup>-</sup>) in a four corners simulation
- Optimum Threshold dispersion of 0.4 mV ( $\sim$ 16 e r.m.s.) @  $I_{DAC} = 200$

## Analog macro and chip layout



- Analog island arrangement (2x2 pixels)
- Analog macro size → 30 x 17  $\mu\text{m}^2$
- 8x32 matrix of readout channels (100 x 25  $\mu\text{m}^2$  pixels)
- Shared 8-bit Time of Arrival Counter (640 MHz)
- Shared 5-bit Time-over-Threshold Counter (40 MHz)
- SPI controller
- 1.7 x 1.5 mm<sup>2</sup> prototype chip submitted in July 2024

